

Features

- 16 Mbit SRAM Multi Chip Module
- Allows 32-, 16- or 8-bit access configuration
- Operating Voltage: 3.3V \pm 0.3V
- Access Time
 - 20 ns, 18 ns for AT68166F
 - <18 ns for AT68166G (in development prototypes in Q4 2007)
- Power Consumption
 - Active: 620 mW per byte (Max) @ 18ns - 415 mW per byte (Max) @ 50ns ⁽¹⁾
 - Standby: 13 mW (Typ)
- Military Temperature Range: -55 to +125°C
- TTL-Compatible Inputs and Outputs
- Asynchronous
- Die manufactured on Atmel 0.25 μ m Radiation Hardened Process
- No Single Event Latch Up below LET Threshold of 80 MeV/mg/cm²
- Tested up to a Total Dose of 300 krad (Si) according to MIL-STD-883 Method 1019
- ESD Better than 4000V
- Quality Grades:
 - QML-Q or V with SMD 5962-06229
 - ESCC
- 950 Mils Wide MQFP 68 Package
- Mass : 8.5 grams

Note: 1. Only for AT68166F-18. 450mW for AT68166F-20.

Description

The AT68166F/G is a 16Mbit SRAM packaged in a hermetic Multi Chip Module (MCM) for space applications.

The AT68166F/G MCM incorporates four 4Mbit AT60142FT SRAM dice. It can be organized as either one bank of 512Kx8, two banks of 512Kx16 or four banks of 512Kx8. It combines rad-hard capabilities, a latch-up threshold of 80MeV.cm²/mg, a Multiple Bit Upset immunity and a total dose tolerance of 300Krad, with a fast access time.

The MCM packaging technology allows a reduction of the PCB area by 50% with a weight savings of 75% compared to four 4Mbit packages.

Thanks to the small size of the 4Mbit SRAM die, Atmel has been able to accommodate the assembly of the four dice on one side of the package which facilitates the power dissipation.

The compatibility with other products allows designers to easily migrate to the Atmel AT68166F/G memory.

The AT68166F/G is powered at 3.3V.

The AT68166F/G is processed according to the test methods of the latest revision of the MIL-PRF-38535 or the ESCC 9000.



Rad Hard
16 MegaBit
3.3V
**SRAM Multi-
Chip Module**

AT68166F
AT68166G

7747A-AERO-07/07



Block Diagram **Figure 1.** AT68166F/G Block Diagram

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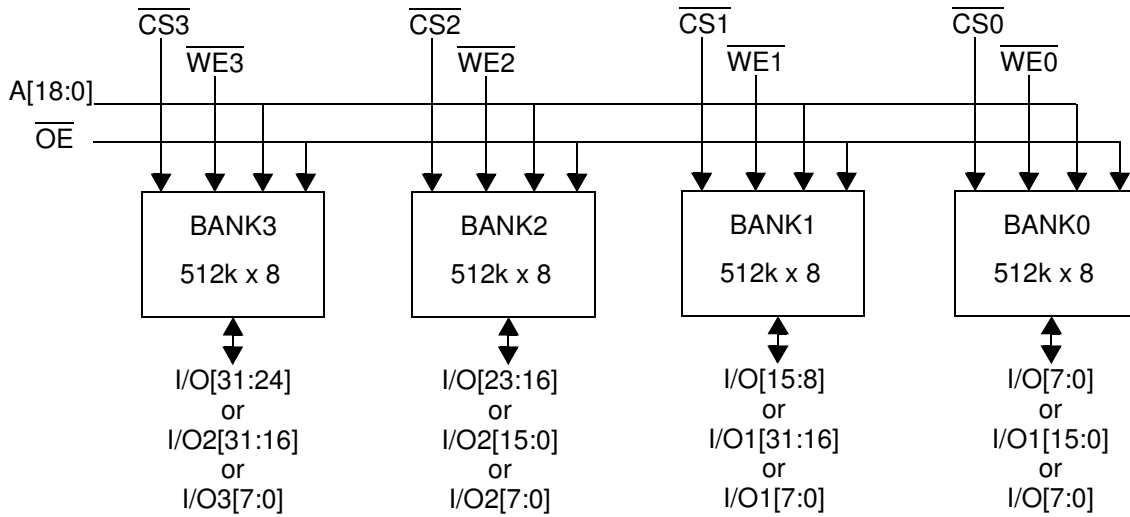
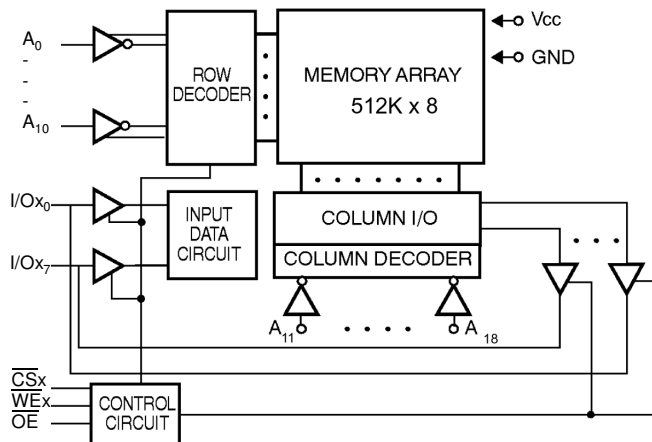


Figure 2. 512K x 8 Banks Block Diagram (AT60142F/G)



Packages

AT68166F and AT68166G are packed in MQFP68.

	Access Time		
	20 ns	18 ns	<18 ns
AT68166F	YM	YS	
AT68166G			YS

The pin assignment depends on the access time. There are 2 versions:

- YM package where 3 pins are not connected.
- YS package where the 3 above pins are connected to GND or V_{CC}.

Pin Configuration

Table 1. AT68166F/G pin assignment in YS package

Lead	Signal	Lead	Signal	Lead	Signal	Lead	Signal
1	I/O0[0]	18	VCC	35	I/O3[7]	52	VCC
2	I/O0[1]	19	A11	36	I/O3[6]	53	A10
3	I/O0[2]	20	A12	37	I/O3[5]	54	A9
4	I/O0[3]	21	A13	38	I/O3[4]	55	A8
5	I/O0[4]	22	A14	39	I/O3[3]	56	A7
6	I/O0[5]	23	A15	40	I/O3[2]	57	A6
7	I/O0[6]	24	A16	41	I/O3[1]	58	WE0
8	I/O0[7]	25	CS0	42	I/O3[0]	59	CS3
9	GND	26	OE	43	GND	60	GND
10	I/O1[0]	27	CS1	44	I/O2[7]	61	CS2
11	I/O1[1]	28	A17	45	I/O2[6]	62	A5
12	I/O1[2]	29	WE1	46	I/O2[5]	63	A4
13	I/O1[3]	30	WE2	47	I/O2[4]	64	A3
14	I/O1[4]	31	WE3	48	I/O2[3]	65	A2
15	I/O1[5]	32	A18	49	I/O2[2]	66	A1
16	I/O1[6]	33	GND	50	I/O2[1]	67	A0
17	I/O1[7]	34	VCC	51	I/O2[0]	68	VCC

Notes: 1. In YM package leads 33, 34 and 68 are not connected.

Figure 3. AT68166F pin assignment in YM package

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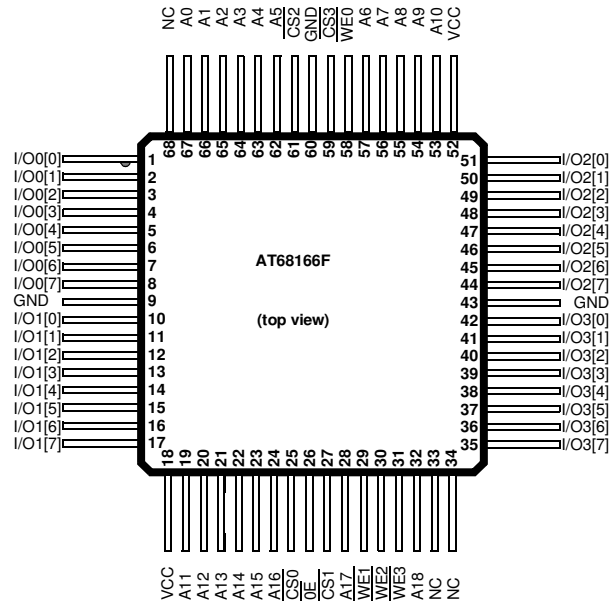
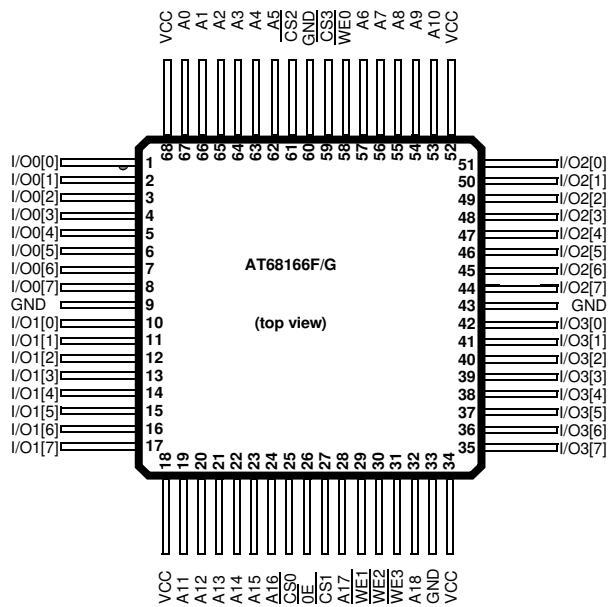


Figure 4. AT68166F/G pin assignment in YS package



Pin Description

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Table 2. Pin Names

Name	Description
A0 - A18	Address Inputs
I/O0 - I/O31	Data Input/Output
$\overline{CS0}$ - $\overline{CS3}$	Chip Select
$\overline{WE0}$ - $\overline{WE3}$	Write Enable
\overline{OE}	Output Enable
VCC	Power Supply
GND ⁽¹⁾	Ground

Note: 1. The package lid is connected to GND

Table 3. Truth Table⁽¹⁾

\overline{CSx}	\overline{WEx}	\overline{OE}	Inputs/Outputs	Mode
H	X	X	Z	Standby
L	H	L	Data Out	Read
L	L	X	Data In	Write
L	H	H	Z	Output Disable

Note: 1. L=low, H=high, X= H or L, L=high impedance.



Electrical Characteristics

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Absolute Maximum Ratings*

Supply Voltage to GND Potential:.....	-0.5V + 4.6V
DC Input Voltage:.....	GND -0.5V to 4.6V
DC Output Voltage High Z State:.....	GND -0.5V to 4.6V
Storage Temperature:.....	-65°C to + 150°C
Output Current Into Outputs (Low):	20 mA
Electro Statics Discharge Voltage:.....	> 4000V (MIL STD 883D Method 3015.3)

*NOTE:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Military Operating Range

Operating Voltage	Operating Temperature
3.3 ± 0.3V	-55°C to + 125°C

Recommended DC Operating Conditions

Parameter	Description	Min	Typ	Max	Unit
V _{CC}	Supply voltage	3	3.3	3.6	V
GND	Ground	0.0	0.0	0.0	V
V _{IL}	Input low voltage	GND - 0.3	0.0	0.8	V
V _{IH}	Input high voltage	2.2	–	V _{CC} + 0.3	V

Capacitance

Parameter	Description	Min	Typ	Max	Unit
C _{in} ⁽¹⁾ (OE and Ax)	Input capacitance	–	–	48	pF
C _{in} ⁽¹⁾ (CSx and WEx)	Input capacitance	–	–	12	pF
C _{io} ⁽¹⁾	I/O capacitance	–	–	12	pF

Note: 1. Guaranteed but not tested.

DC Parameters

Parameter	Description	Minimum	Typical	Maximum	Unit
IIX ⁽¹⁾	Input leakage current	-1	-	1	μA
IOZ ⁽¹⁾	Output leakage current	-1	-	1	μA
VOL ⁽²⁾	Output low voltage	-	-	0.4	V
VOH ⁽³⁾	Output high voltage	2.4	-	-	V

- Notes:
1. $GND < V_{IN} < V_{CC}$, $GND < V_{OUT} < V_{CC}$ Output Disabled.
 2. V_{CC} min. $I_{OL} = 8$ mA
 3. V_{CC} min. $I_{OH} = -4$ mA

Consumption

Symbol	Description	TAVAV/TAVAW Test Condition	AT68166F-20	AT68166F-18	Unit	Value
$I_{CCSB}^{(1)}$	Standby Supply Current	-	10	7	mA	max
$I_{CCSB1}^{(2)}$	Standby Supply Current	-	8	6	mA	max
$I_{CCOP}^{(3)}$ Read per byte	Dynamic Operating Current	18 ns 20 ns 50 ns 1 μs	- 170 85 15	170 165 80 12	mA	max
$I_{CCOP}^{(4)}$ Write per byte	Dynamic Operating Current	18 ns 20 ns 50 ns 1 μs	- 150 125 110	145 140 115 105	mA	max

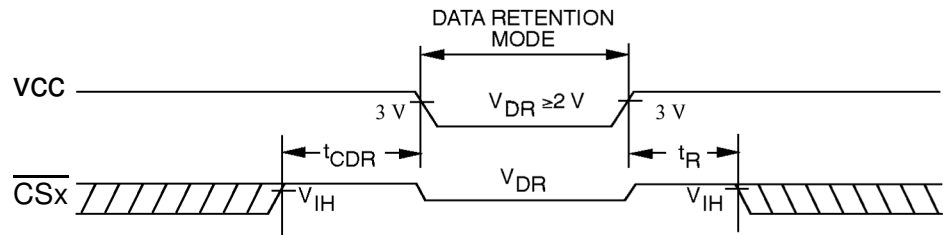
- Notes:
1. All $\overline{CSx} \geq V_{IH}$
 2. All $\overline{CSx} \geq V_{CC} - 0.3V$
 3. $F = 1/T_{TAVAV}$, $I_{out} = 0$ mA, $\overline{WEX} = \overline{OE} = V_{IH}$, $V_{IN} = GND/V_{CC}$, V_{CC} max.
 4. $F = 1/T_{TAVAW}$, $I_{out} = 0$ mA, $\overline{WEX} = V_{IL}$, $\overline{OE} = V_{IH}$, $V_{IN} = GND/V_{CC}$, V_{CC} max.

Data Retention Mode

Atmel CMOS RAM's are designed with battery backup in mind. Data retention voltage and supply current are guaranteed over temperature. The following rules insure data retention:

1. During data retention chip select \overline{CSx} must be held high within V_{CC} to $V_{CC} - 0.2V$.
2. Output Enable (\overline{OE}) should be held high to keep the RAM outputs high impedance, minimizing power dissipation.
3. During power-up and power-down transitions \overline{CSx} and \overline{OE} must be kept between $V_{CC} + 0.3V$ and 70% of V_{CC} .
4. The RAM can begin operation $> t_R$ ns after V_{CC} reaches the minimum operation voltages (3V).

Figure 5. Data Retention Timing



Data Retention Characteristics

Parameter	Description	Min	Typ $T_A = 25^\circ C$	Max	Unit
V_{CCDR}	V_{CC} for data retention	2.0	–	–	V
t_{CDR}	Chip deselect to data retention time	0.0	–	–	ns
t_R	Operation recovery time	$t_{AVAV}^{(1)}$	–	–	ns
$I_{CCDR}^{(2)}$	Data retention current	–	3	6 (AT68166F-20)	mA
				4.5 (AT68166F-18)	

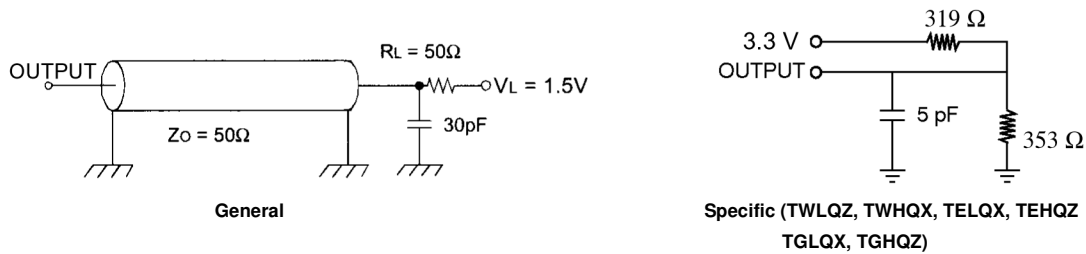
1. T_{AVAV} = Read cycle time.
2. All $CSx = V_{CC}$, $V_{IN} = GND/V_{CC}$.

AC Characteristics

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Temperature Range:..... -55 +125°C
 Supply Voltage: 3.3 ±0.3V
 Input Pulse Levels: GND to 3.0V
 Input Rise and Fall Times:..... 3ns (10 - 90%)
 Input and Output Timing Reference Levels: 1.5V
 Output Loading I_{OL}/I_{OH} :..... See Figure 3

Figure 6. AC Test Loads Waveforms



Write Cycle

Table 4. Write cycle timings⁽¹⁾

Symbol	Parameter	AT68166F-20		AT68166F-18		Unit
		min	max	min	max	
TAVAW	Write cycle time	20	-	18	-	ns
TAVWL	Address set-up time	2	-	2	-	ns
TAVWH	Address valid to end of write	14	-	11	-	ns
TDVWH	Data set-up time	9	-	8	-	ns
TELWH	\overline{CS} low to write end	12	-	12	-	ns
TWLQZ	Write low to high $Z^{(2)}$	-	10	-	8	ns
TWLWH	Write pulse width	12	-	9	-	ns
TWHAX	Address hold from end of write	0	-	0	-	ns
TWHDX	Data hold time	2	-	1	-	ns
TWHQX	Write high to low $Z^{(2)}$	5	-	3	-	ns

- Notes: 1. Timings figures applicable for 8-bit, 16-bit and 32-bit mode.
 2. Parameters guaranteed, not tested, with output loading 5 pF. (See "AC Test Loads Waveforms" on page 9.)

Figure 7. Write Cycle 1. \overline{WE} Controlled, \overline{OE} High During Write

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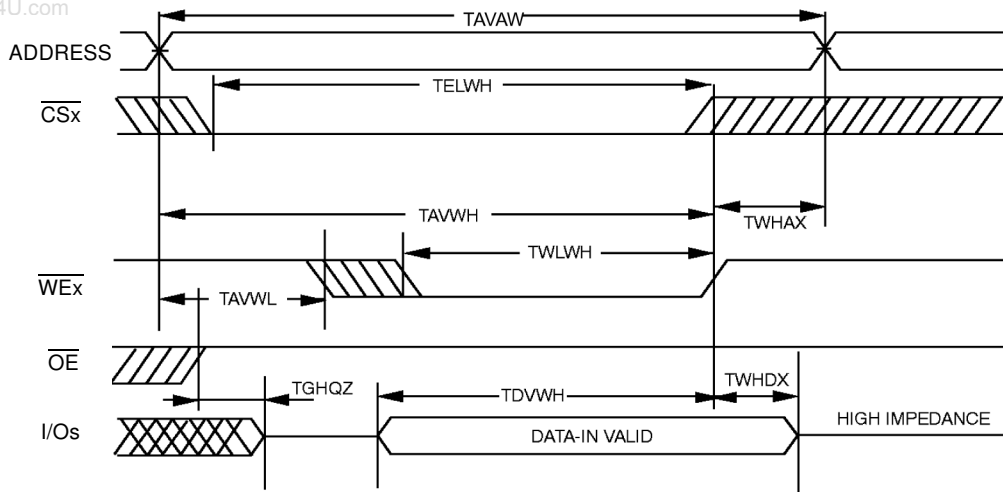


Figure 8. Write Cycle 2. \overline{WE} Controlled, \overline{OE} Low

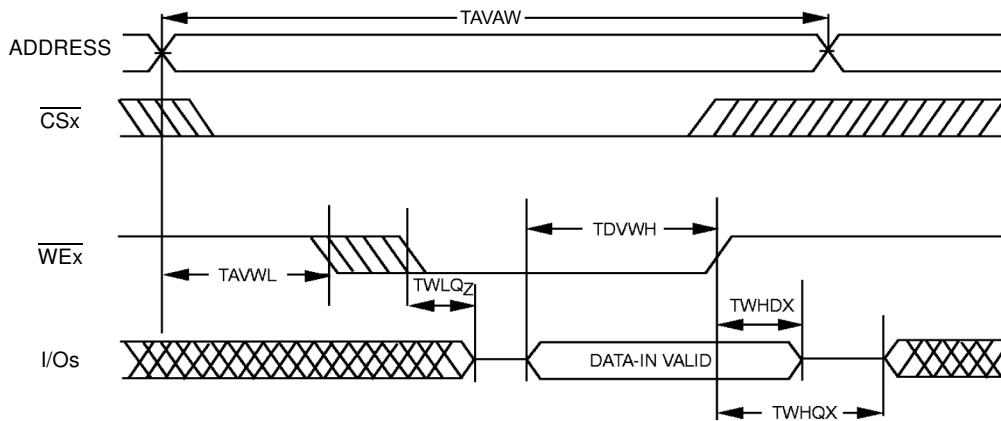
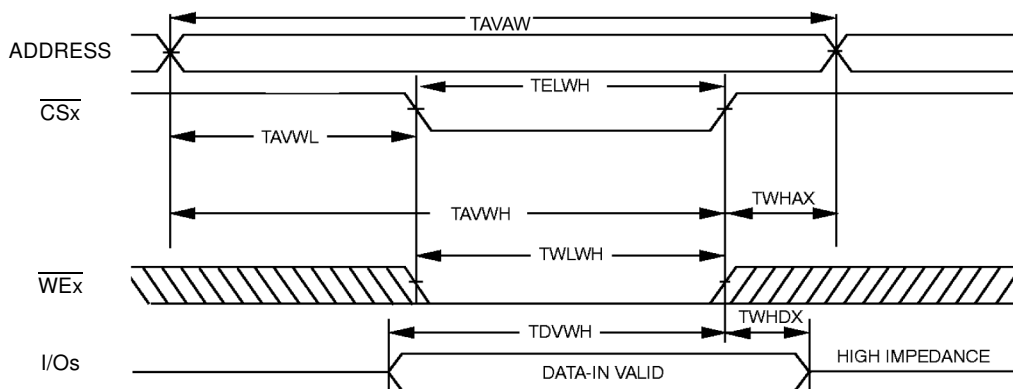


Figure 9. Write Cycle 3. \overline{CS} Controlled



The internal write time of the memory is defined by the overlap of \overline{CS} Low and \overline{WE} LOW. Both signals must be activated to initiate a write and either signal can terminate a write by going in active mode. The data input setup and hold timing should be referenced to the active edge of the signal that terminates the write. Data out is high impedance if $\overline{OE} = V_{IH}$.

Read Cycle

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Table 5. Read cycle timings⁽¹⁾

Symbol	Parameter	AT68166F-20		AT68166F-18		Unit
		min	max	min	max	
TAVAV	Read cycle time	20	-	18	-	ns
TAVQV	Address access time	-	20	-	18	ns
TAVQX	Address valid to low Z	5	-	5	-	ns
TELQV	Chip-select access time	-	20	-	18	ns
TELQX	\overline{CS} low to low Z ⁽²⁾	5	-	5	-	ns
TEHQZ	\overline{CS} high to high Z ⁽²⁾	-	9	-	8	ns
TGLQV	Output Enable access time	-	11	-	8	ns
TGLQX	\overline{OE} low to low Z ⁽²⁾	2	-	2	-	ns
TGHQZ	\overline{OE} high to high Z ⁽²⁾	-	9	-	8	ns

- Notes: 1. Timings figures applicable for 8-bit, 16-bit and 32-bit mode.
 2. Parameters guaranteed, not tested, with output loading 5 pF. (See “AC Test Loads Waveforms” on page 9.)

Figure 10. Read Cycle nb 1: Address Controlled ($\overline{CS} = \overline{OE} = V_{IL}$, $\overline{WE} = V_{IH}$)

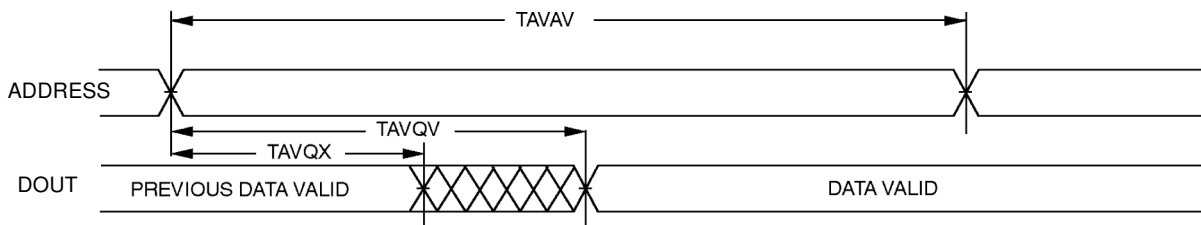
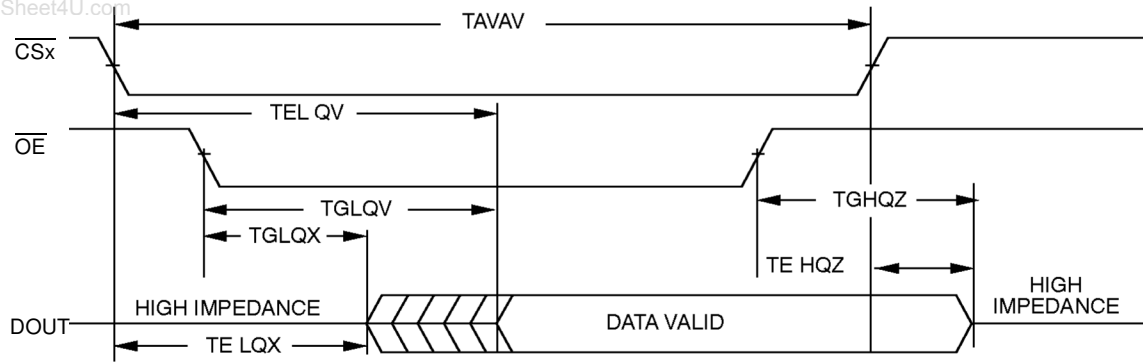


Figure 11. Read Cycle nb 2: Chip Select Controlled ($\overline{WE} = V_{IH}$)

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Typical Applications

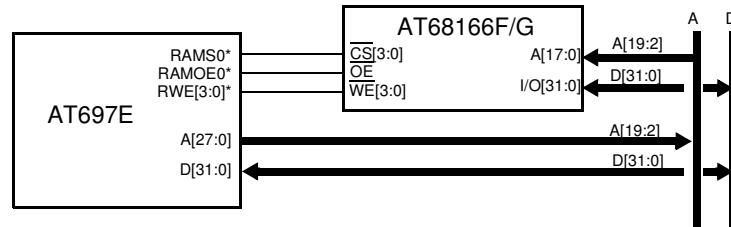
This section presents some standard implementations of the AT68166F/G in application.

32-bit mode application

When used on a 32-bit (word) application, the module shall be connected as follow :

- The 32 lines of data are connected to distinct data lines
- The four \overline{CS}_x are connected together and linked to a single host \overline{CS} output
- Each one of the four \overline{WE}_x is connected to a dedicated \overline{WE} line on the host to allow byte, half word and word format write.

Figure 12. 32-bit typical application (1 SRAM bank)

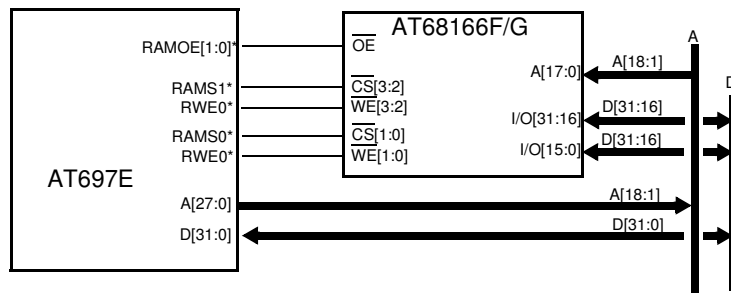


16-bit mode application

When used on a 16-bit (half word) application, the module can be connected as presented in the following figure. This allows use of a single AT68166F/G part for two SRAM memory banks.

All input controls of the AT68166F/G not used in the application shall be pulled-up.

Figure 13. 16-bit typical application (two SRAM banks)



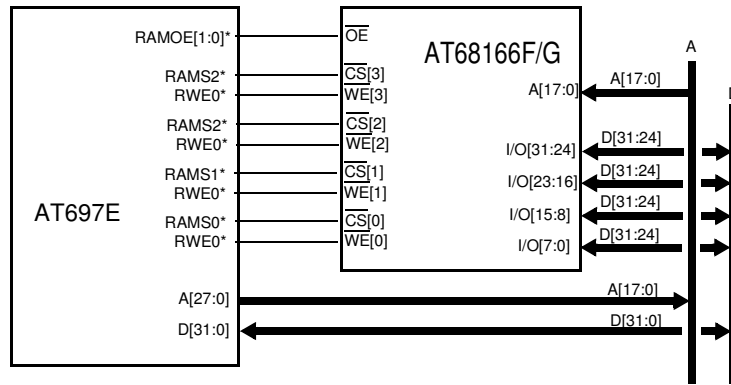
8-bit mode application

When used on a 8-bit (byte) application, the module can be connected as presented in the following figure. This allows use of a single AT68166F/G part for up to four SRAM memory banks.

All input controls of the AT68166F/G not used in the application shall be pulled-up.

Figure 14. 8-bit typical application (two SRAM banks)

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Ordering Information

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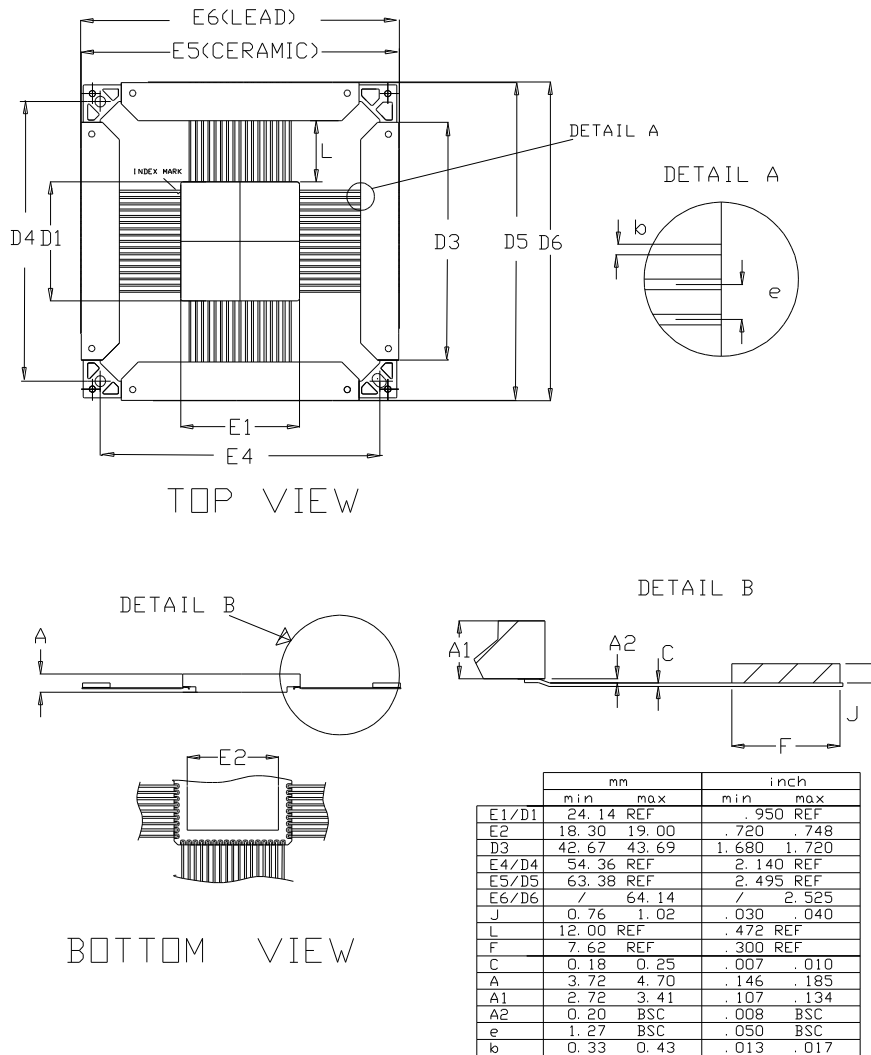
Part Number	Temperature Range	Speed	Package	Flow
AT68166F				
AT68166F-YM20-E	25°C	20 ns	MQFP68	Engineering Samples
5962-0622902QXC	-55° to +125°C	20 ns	MQFP68	QML Q
5962-0622902VXC	-55° to +125°C	20 ns	MQFP68	QML V
5962R0622902VXC	-55° to +125°C	20 ns	MQFP68	QML V RHA
AT68166F-YM20-SCC	-55° to +125°C	20 ns	MQFP68	ESCC
AT68166F-YS18-E	25°C	18 ns	MQFP68	Engineering Samples
AT68166F-YS18-MQ ⁽¹⁾	-55° to +125°C	18 ns	MQFP68	QML Q
AT68166F-YS18-SV ⁽¹⁾	-55° to +125°C	18 ns	MQFP68	QML V
AT68166F-YS18-SR ⁽¹⁾	-55° to +125°C	18 ns	MQFP68	QML V RHA
AT68166F-YS18-SCC ⁽¹⁾	-55° to +125°C	18 ns	MQFP68	ESCC

Note: 1. Will be replaced by SMD part number when available.

Package Drawings

68-lead Quad Flat Pack (950 Mils) with non conductive tie bar

68 LEADS FLAT PACK CERAMIC TIE BAR



Note: Lid is connected to Ground.
 Note: YM and YS package drawings are identical.



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Atmel Corporation

2325 Orchard Parkway
San Jose, CA 95131, USA
Tel: 1(408) 441-0311
Fax: 1(408) 487-2600

Regional Headquarters

Europe

Atmel Sarl
Route des Arsenaux 41
Case Postale 80
CH-1705 Fribourg
Switzerland
Tel: (41) 26-426-5555
Fax: (41) 26-426-5500

Asia

Room 1219
Chinachem Golden Plaza
77 Mody Road Tsimshatsui
East Kowloon
Hong Kong
Tel: (852) 2721-9778
Fax: (852) 2722-1369

Japan

9F, Tonetsu Shinkawa Bldg.
1-24-8 Shinkawa
Chuo-ku, Tokyo 104-0033
Japan
Tel: (81) 3-3523-3551
Fax: (81) 3-3523-7581

Atmel Operations

Memory

2325 Orchard Parkway
San Jose, CA 95131, USA
Tel: 1(408) 441-0311
Fax: 1(408) 436-4314

Microcontrollers

2325 Orchard Parkway
San Jose, CA 95131, USA
Tel: 1(408) 441-0311
Fax: 1(408) 436-4314

La Chantrerie
BP 70602
44306 Nantes Cedex 3, France
Tel: (33) 2-40-18-18-18
Fax: (33) 2-40-18-19-60

ASIC/ASSP/Smart Cards

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Tel: (33) 4-42-53-60-00
Fax: (33) 4-42-53-60-01

1150 East Cheyenne Mtn. Blvd.
Colorado Springs, CO 80906, USA
Tel: 1(719) 576-3300
Fax: 1(719) 540-1759

Scottish Enterprise Technology Park
Maxwell Building
East Kilbride G75 0QR, Scotland
Tel: (44) 1355-803-000
Fax: (44) 1355-242-743

RF/Automotive

Theresienstrasse 2
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74025 Heilbronn, Germany
Tel: (49) 71-31-67-0
Fax: (49) 71-31-67-2340

1150 East Cheyenne Mtn. Blvd.
Colorado Springs, CO 80906, USA
Tel: 1(719) 576-3300
Fax: 1(719) 540-1759

Biometrics/Imaging/Hi-Rel MPU/

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Avenue de Rochepleine
BP 123
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Tel: (33) 4-76-58-30-00
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